

ABSTRACT

A method is provided for controlling a chemical mechanical polishing (CMP) operation. The method is operative in a CMP apparatus having a plurality of end point detection probes and in which a plurality of process variables can be set to adjust the removal rate across a layer that is to be polished. In accordance with the method, the process variables are adjusted to a first setting and a layer overlying a work piece is polished using that setting. Information from the plurality of end point detection probes is collected and evaluated to determine removal rate of the layer. The process variables are adjusted in response the evaluation and a second layer on a second work piece is polished using the adjusted settings.